METHOD OF FORMING STORAGE NODES IN A DRAM

Appl. No. : 09/851,580 Confirmation No. 3189

Applicant : Jiunn-Ren Hwang et al.

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TC/A.U. : 1795

Examiner : Ruggles, John S

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Customer No.: 27765

Commissioner for Patents

P.O. Box 1450

Alexandria VA 22313-1450

AMENDMENT

Sir:

In response to the Office action of July 10, 2008, please amend the above-identified application as follows:

Amendments to the Specification begin on page 2 of this paper.

Amendments to the Claims are reflected in the listing of claims which begins on page 6 of this paper.

10 Amendments to the Drawings begin on page 8 of this paper.

Remarks/Arguments begin on page 9 of this paper.

An Appendix including amended drawing figures is attached following page 11 of this paper.